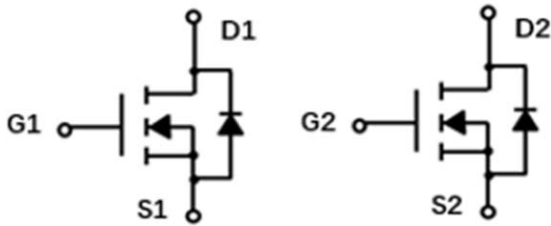
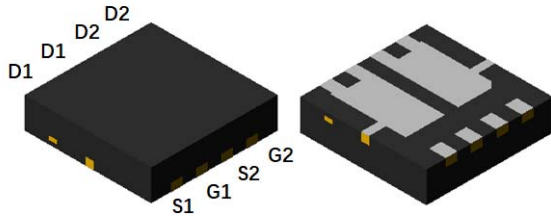


## N-Channel Enhancement Mode Field Effect Transistor

### DFN3.3X3.3



### Product Summary

- $V_{DS}$  30V
- $I_D$  30A
- $R_{DS(ON)}$  (at  $V_{GS} = 10V$ ) < 13mohm
- $R_{DS(ON)}$  (at  $V_{GS} = 4.5V$ ) < 16mohm
- 100% UIS Tested
- 100%  $\nabla V_{DS}$  Tested

### General Description

- Trench Power LV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low  $R_{DS(ON)}$

### Applications

- High current load applications
- Load switch
- Hard switched and high frequency circuits
- Uninterruptible power supply

### ■ Absolute Maximum Ratings ( $I_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{DS}$	30	V
Gate-source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D$	$T_C=25^\circ C$	30
		$T_C=100^\circ C$	21
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	115	A
Total Power Dissipation	$P_D$	$T_C=25^\circ C$	21
		$T_C=100^\circ C$	10.5
Single Pulse Avalanche Energy <sup>B</sup>	$E_{AS}$	140	mJ
Thermal Resistance Junction-to-Case <sup>C</sup>	$R_{\theta JC}$	7.1	$^\circ C/W$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+175	$^\circ C$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJQ3622A	F1	Q3622	5000	10000	100000	13" reel



# YJQ3622A

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	T <sub>J</sub> =25°C		1	μA
			T <sub>J</sub> =55°C		5	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.5	2.5	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> =20A		7.5	13	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> =10A		11.5	16	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =15A, V <sub>GS</sub> =0V		0.85	1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				30	A
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHZ		1015		pF
Output Capacitance	C <sub>oss</sub>			201		
Reverse Transfer Capacitance	C <sub>rss</sub>			164		
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =20V, I <sub>D</sub> =20A		23.6		nC
Gate-Source Charge	Q <sub>gs</sub>			3.9		
Gate-Drain Charge	Q <sub>gd</sub>			7.0		
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =15A, di/dt=100A/us		0.2		
Reverse Recovery Time	t <sub>rr</sub>			5		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =20V, I <sub>D</sub> =2A, R <sub>GEN</sub> =3Ω		7		ns
Turn-on Rise Time	t <sub>r</sub>			19		
Turn-off Delay Time	t <sub>D(off)</sub>			24		
Turn-off fall Time	t <sub>f</sub>			24		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design, while R<sub>θJA</sub> is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.



■ Typical Performance Characteristics

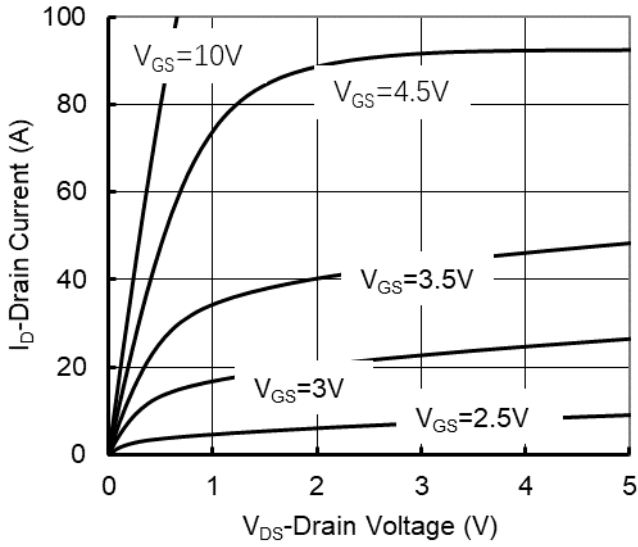


Figure1. Output Characteristics

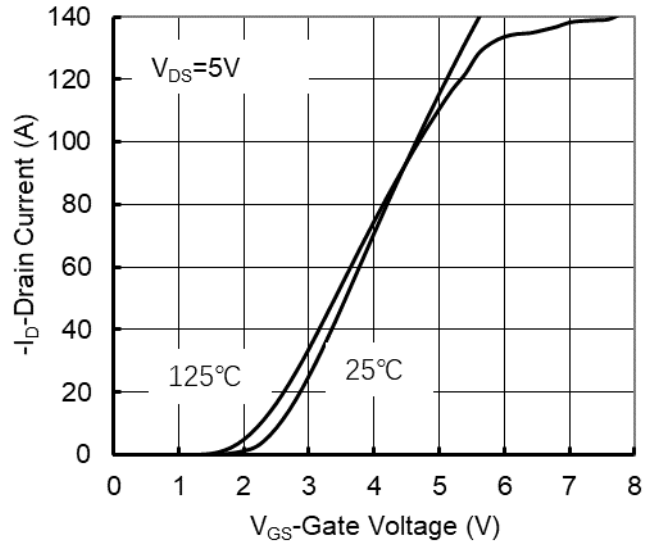


Figure2. Transfer Characteristics

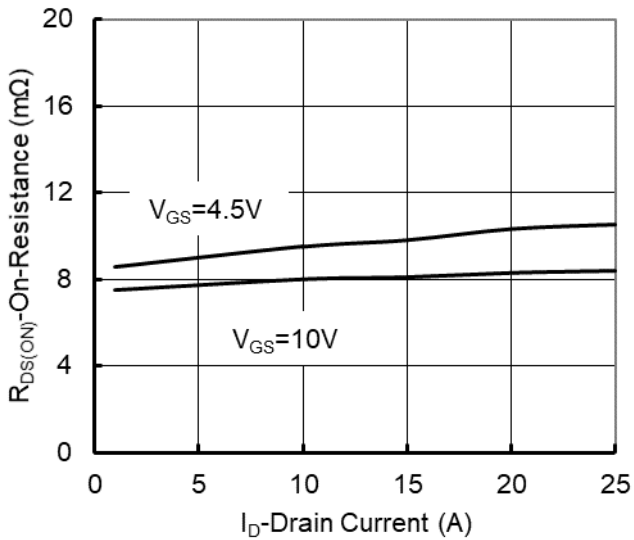


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

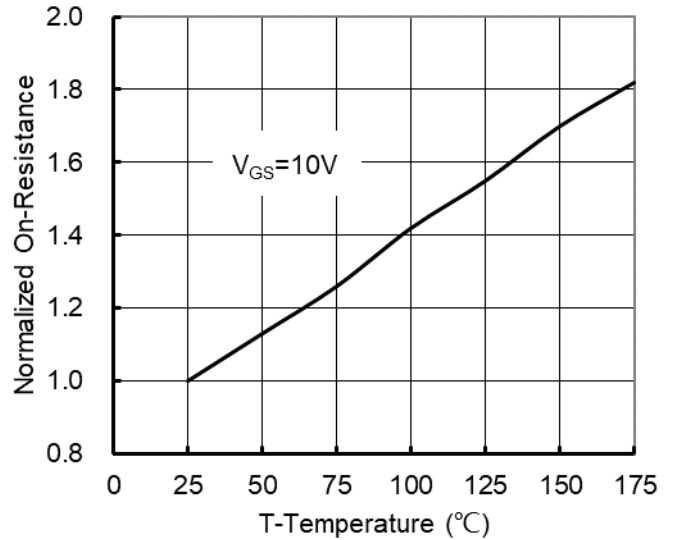


Figure 4: On-Resistance vs. Junction Temperature

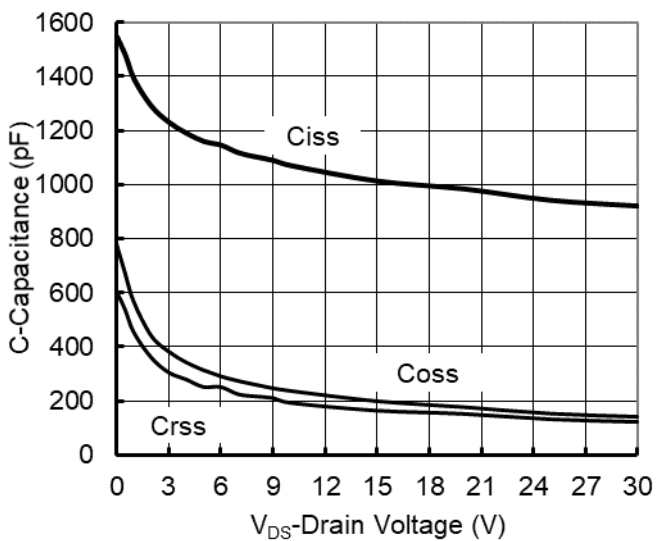


Figure5. Capacitance Characteristics

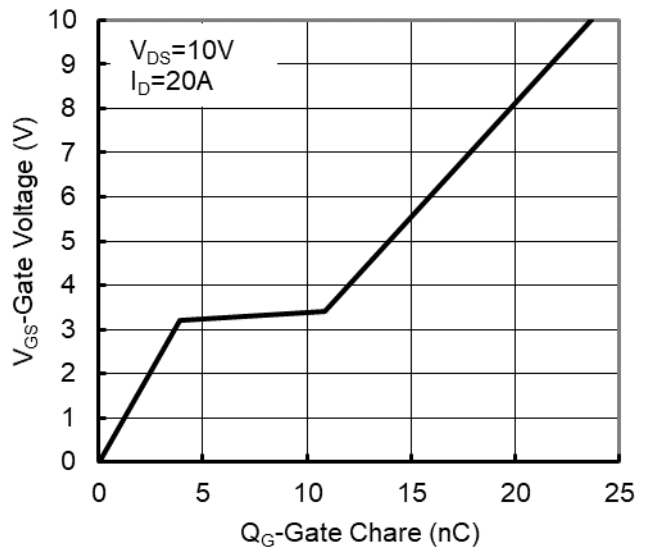


Figure6. Gate Charge

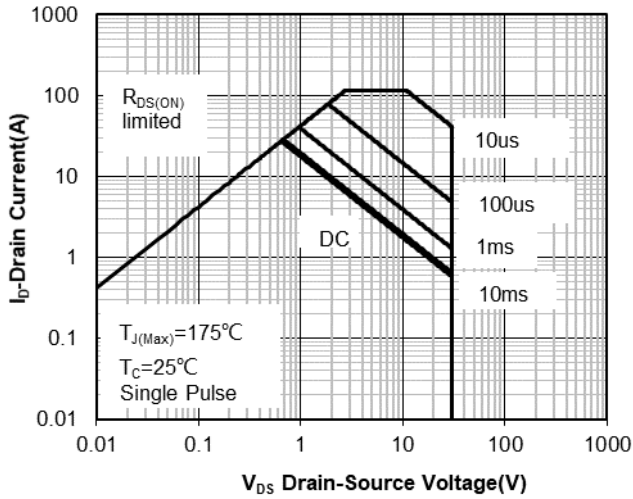


Figure7. Safe Operation Area

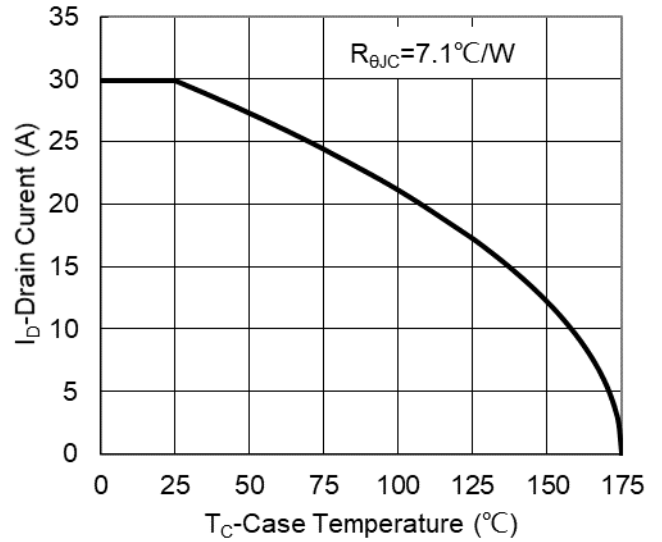


Figure8. Maximum Continuous Drain Current vs Case Temperature

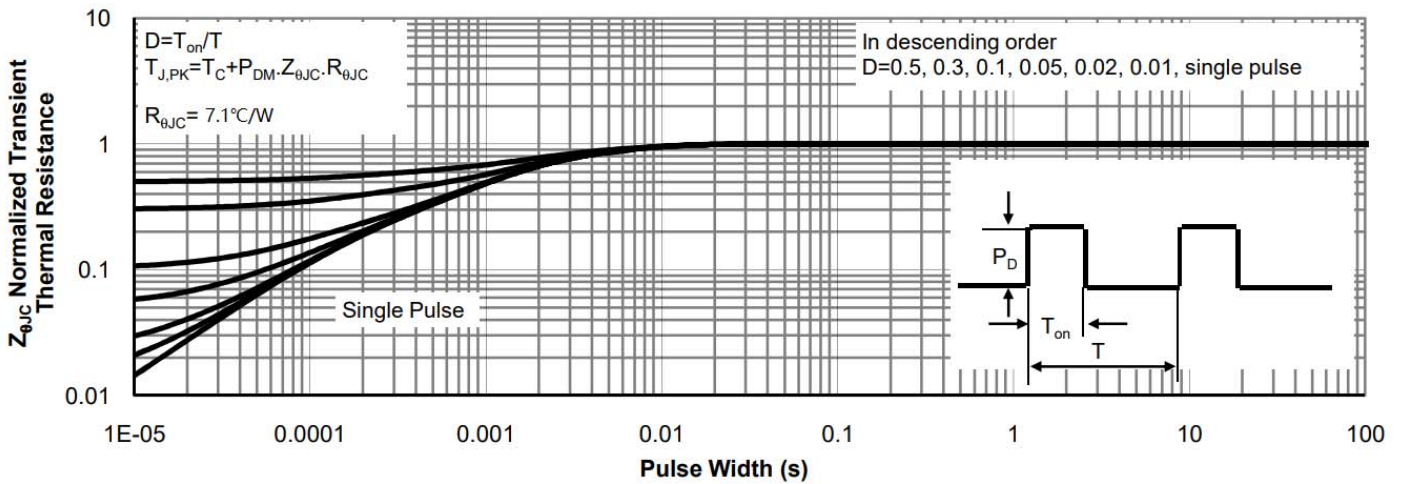
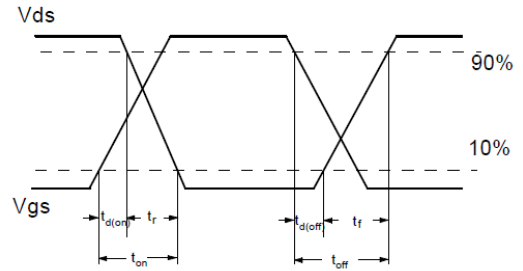
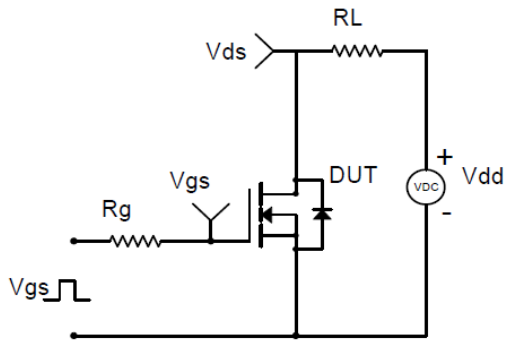
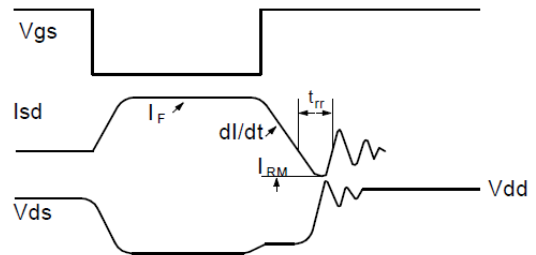
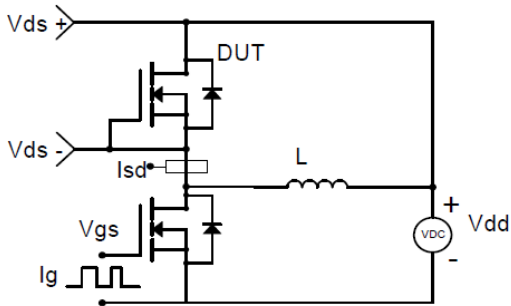


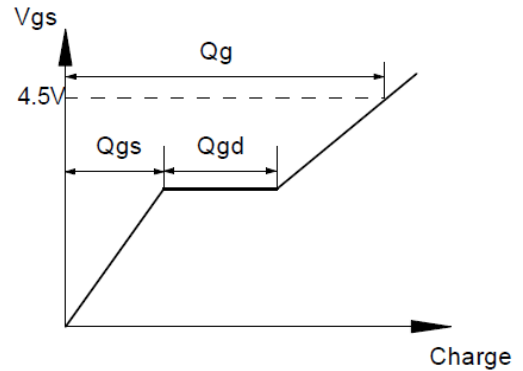
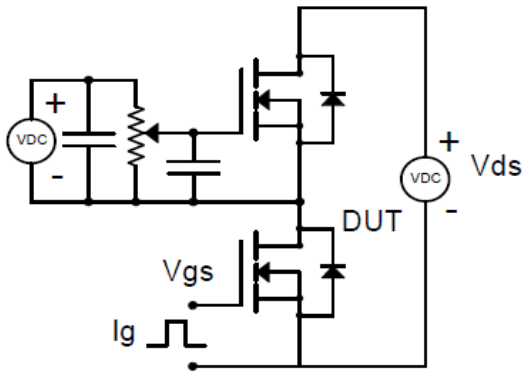
Figure9. Normalized Maximum Transient Thermal Impedance



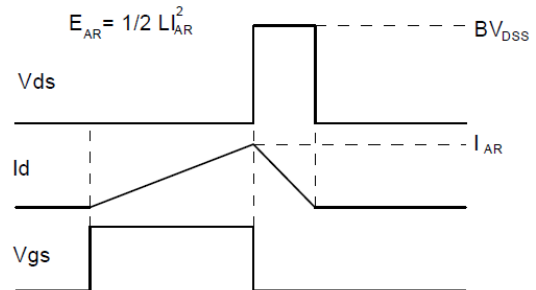
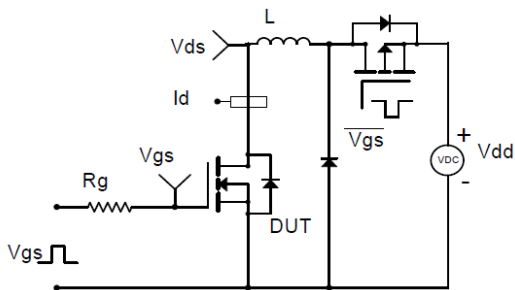
**Resistive Switching Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**



**Gate Charge Test Circuit & Waveform**

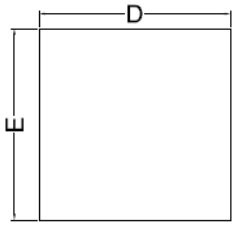


**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**

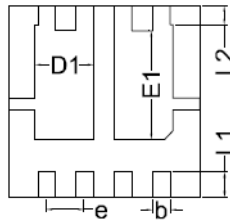


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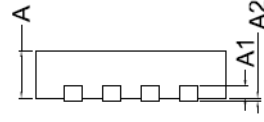
## ■DFN3.3X3.3 Package information



Top View  
正面视图

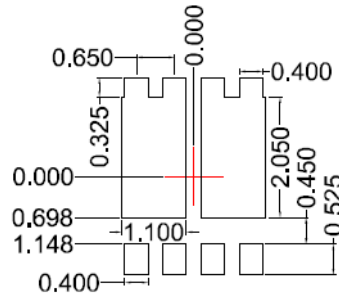


Bottom View  
背面视图



Side View  
侧面视图

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	3.15	3.25	3.35
E	3.15	3.25	3.35
A	0.70	0.80	0.90
A1	0.20 BSC		
A2			0.10
D1	0.90	1.00	1.10
E1	1.75	1.85	1.95
L1	0.325	0.425	0.525
L2	0.325 BSC		
b	0.20	0.30	0.40
e	0.65 BSC		



Suggested Solder Pad Layout  
Top View

Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.10\text{mm}$ .
3. The pad layout is for reference purposes only.



## YJQ3622A

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